SKKH 57/18 E G6

SEMIPACK® 1

Thyristor / Diode Modules

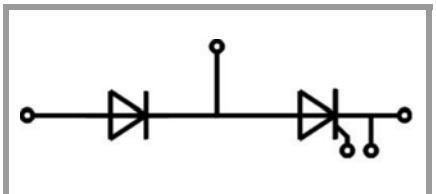
SKKH 57/18 E G6

Features

- Heat transfer through aluminium oxide ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E63532

Typical Applications

- DC motor control (e. g. for machine tools)
- AC motor soft starters
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)



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Absolute Maximum Ratings				
Symbol	**Conditions**		**Values**	**Unit**
Chip				
$I_{T(AV)}$	sinus 180°	T_c = 85 °C	55	A
		T_c = 100 °C	41	A
I_{TSM}	10 ms	T_j = 25 °C	1500	A
		T_j = 130 °C	1200	A
i^2t	10 ms	T_j = 25 °C	11250	kA^2s
i^2t		T_j = 130 °C	7200	kA^2s
V_{RSM}			1900	V
V_{RRM}			1800	V
V_{DRM}			1800	V
$(di/dt)_{cr}$	T_j = 130 °C		140	A/µs
$(dv/dt)_{cr}$	T_j = 130 °C		1000	V/µs
T_j			-40 ... 130	°C
Module				
T_{stg}			-40 ... 125	°C
V_{isol}	a.c.; 50 Hz; r.m.s.	1 min	3000	V
		1 s	3600	V

Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
Chip						
V_T	T_j = 25 °C, I_T = 180 A			1.5	1.75	V
$V_{T(TO)}$	T_j = 130 °C			0.85	1	V
r_T	T_j = 130 °C			4.00	4.80	mΩ
I_{DD};I_{RD}	T_j = 130 °C, V_{DD} = V_{DRM}; V_{RD} = V_{RRM}				20	mA
t_{gd}	T_j = 25 °C, I_G = 1 A, di_G/dt = 1 A/µs			1		µs
t_{gr}	V_D = 0.67 * V_{DRM}			2		µs
t_q	T_j = 130 °C			170		µs
I_H	T_j = 25 °C			150	250	mA
I_L	T_j = 25 °C, R_G = 33 Ω			300	600	mA
V_{GT}	T_j = 25 °C, d.c.		2.5			V
I_{GT}	T_j = 25 °C, d.c.		100			mA
V_{GD}	T_j = 130 °C, d.c.				0.25	V
I_{GD}	T_j = 130 °C, d.c.				4	mA
$R_{th(j-c)}$	cont.	per chip			0.470	K/W
		per module			0.235	K/W
$R_{th(j-c)}$	sin. 180°	per chip			0.490	K/W
		per module			0.245	K/W
$R_{th(j-c)}$	rec. 120°	per chip			0.510	K/W
		per module			0.255	K/W
Module						
$R_{th(c-s)}$	chip			0.22		K/W
	module			0.11		K/W
M_s	to heatsink M5		4.25		5.75	Nm
M_t	to terminals M5		2.55		3.45	Nm
a					5 * 9,81	m/s^2
w				75		g

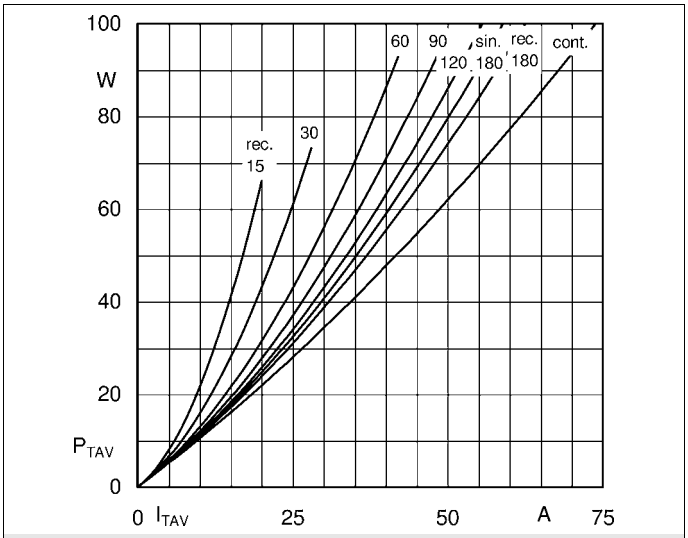


Fig. 1L: Max. power dissipation per chip vs. on-state current

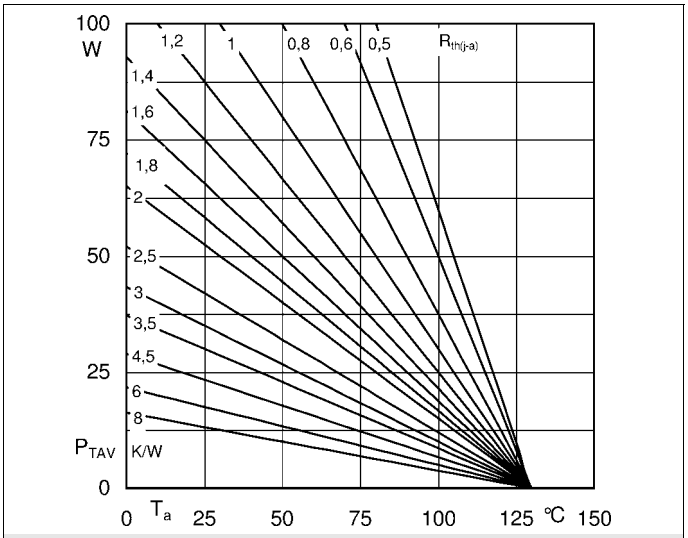


Fig. 1R: Max. power dissipation per chip vs. ambient temperature

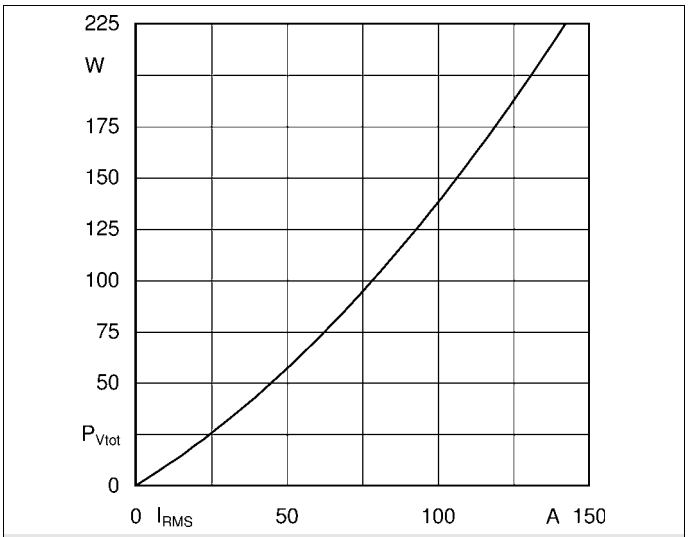


Fig. 2L: Max. power dissipation of one module vs. rms current

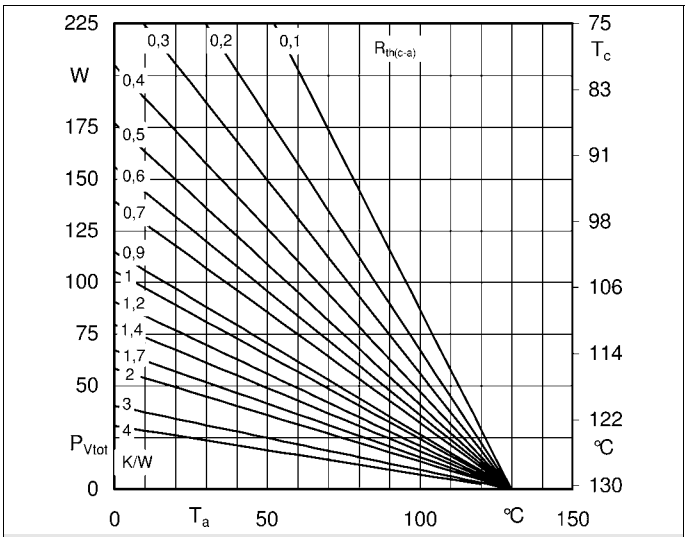


Fig. 2R: Max. power dissipation of one module vs. case temperature

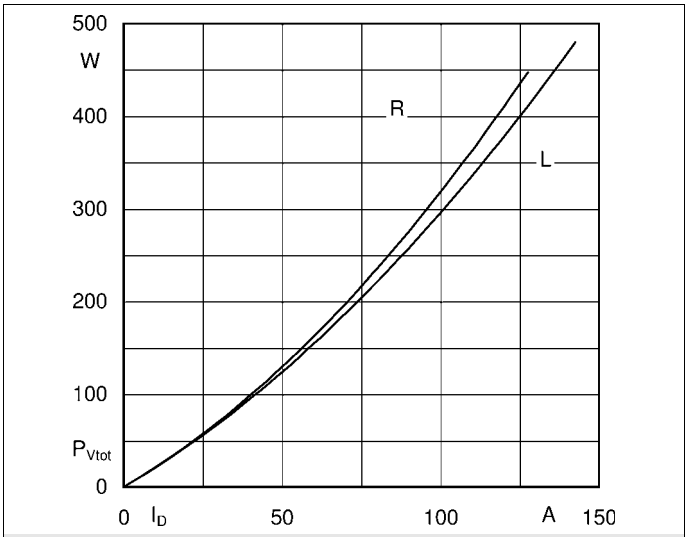


Fig. 3L: Max. power dissipation of two modules vs. direct current

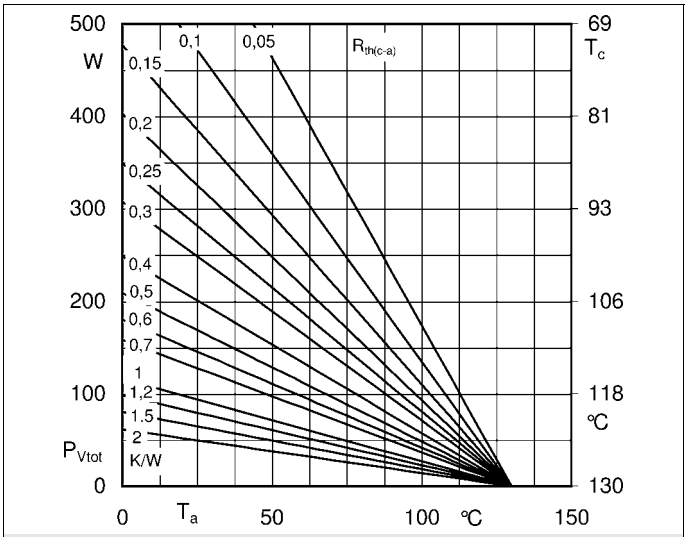


Fig. 3R: Max. power dissipation of two modules vs. case temperature

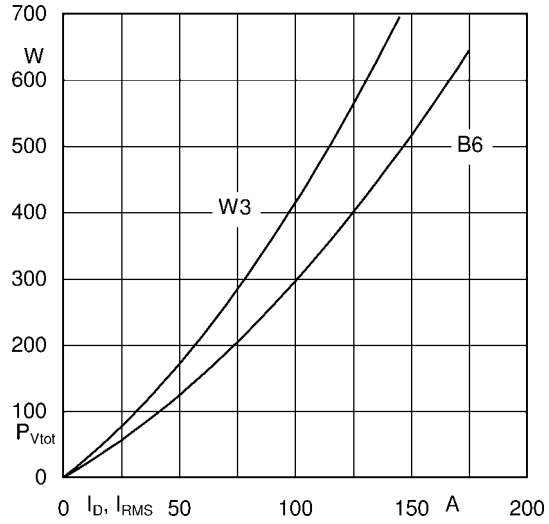


Fig. 4L: Max. power dissipation of three modules vs. direct current

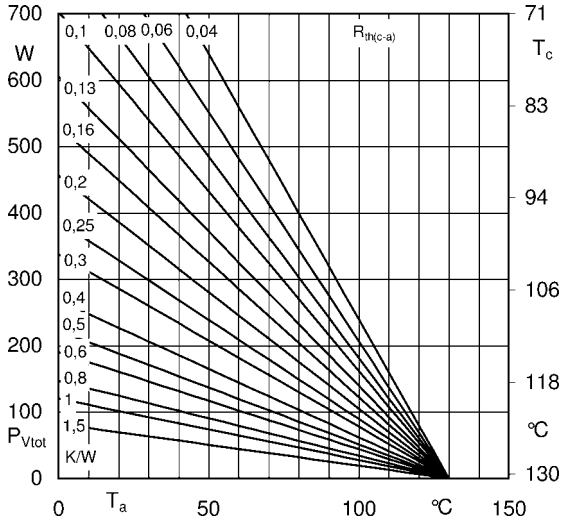


Fig. 4R: Max. power dissipation of three modules vs. case temperature

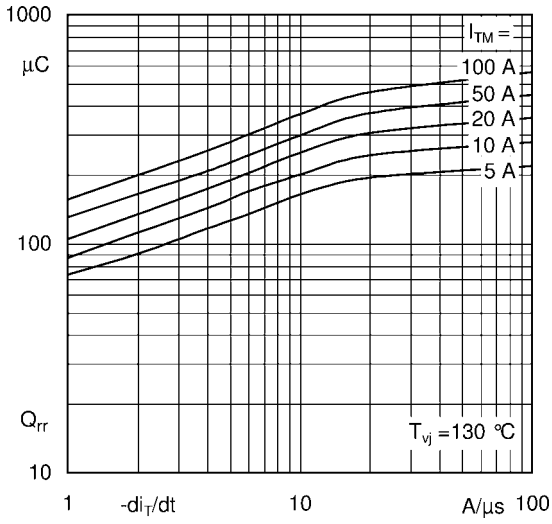


Fig. 5: Recovered charge vs. current decrease

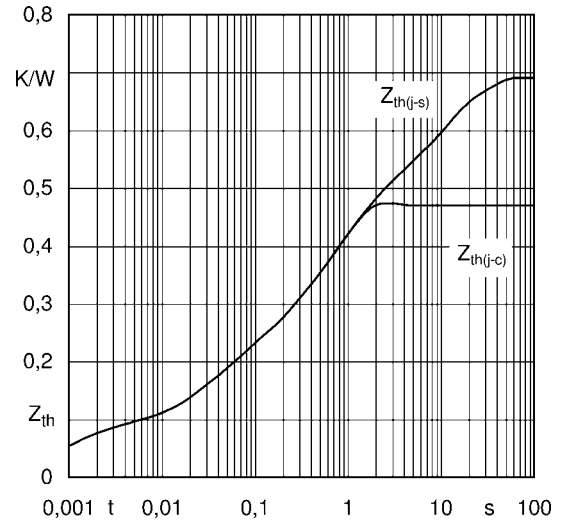


Fig. 6: Transient thermal impedance vs. time

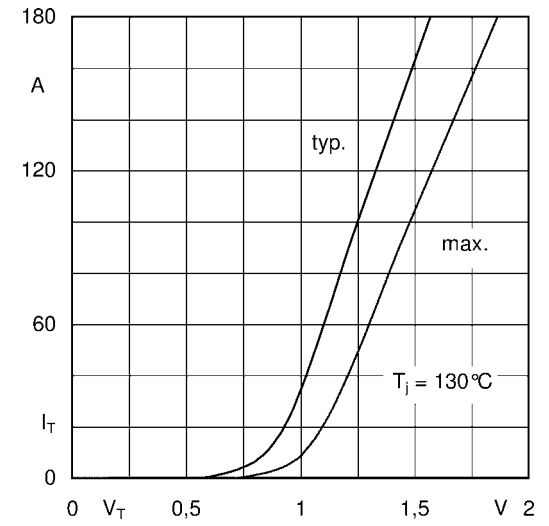


Fig. 7: On-state characteristics

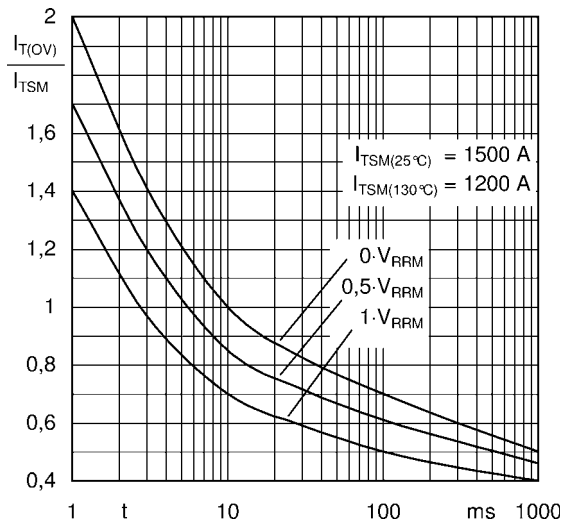


Fig. 8: Surge overload current vs. time

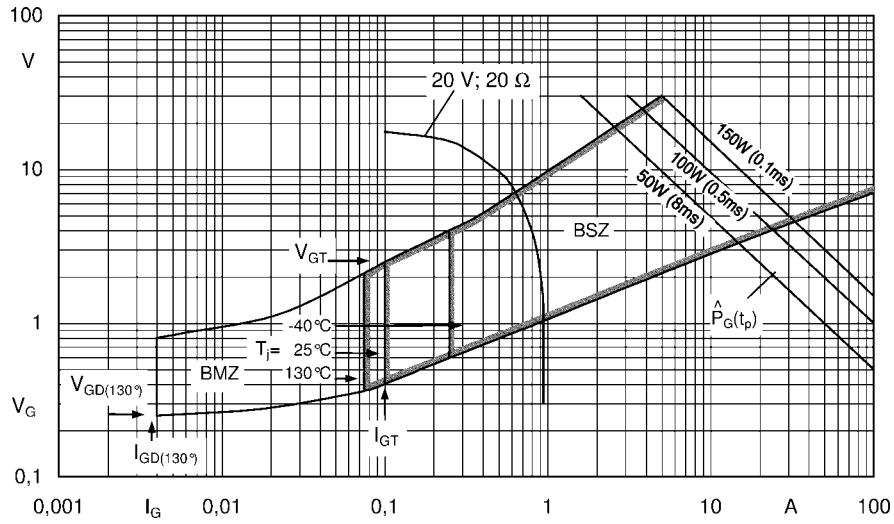
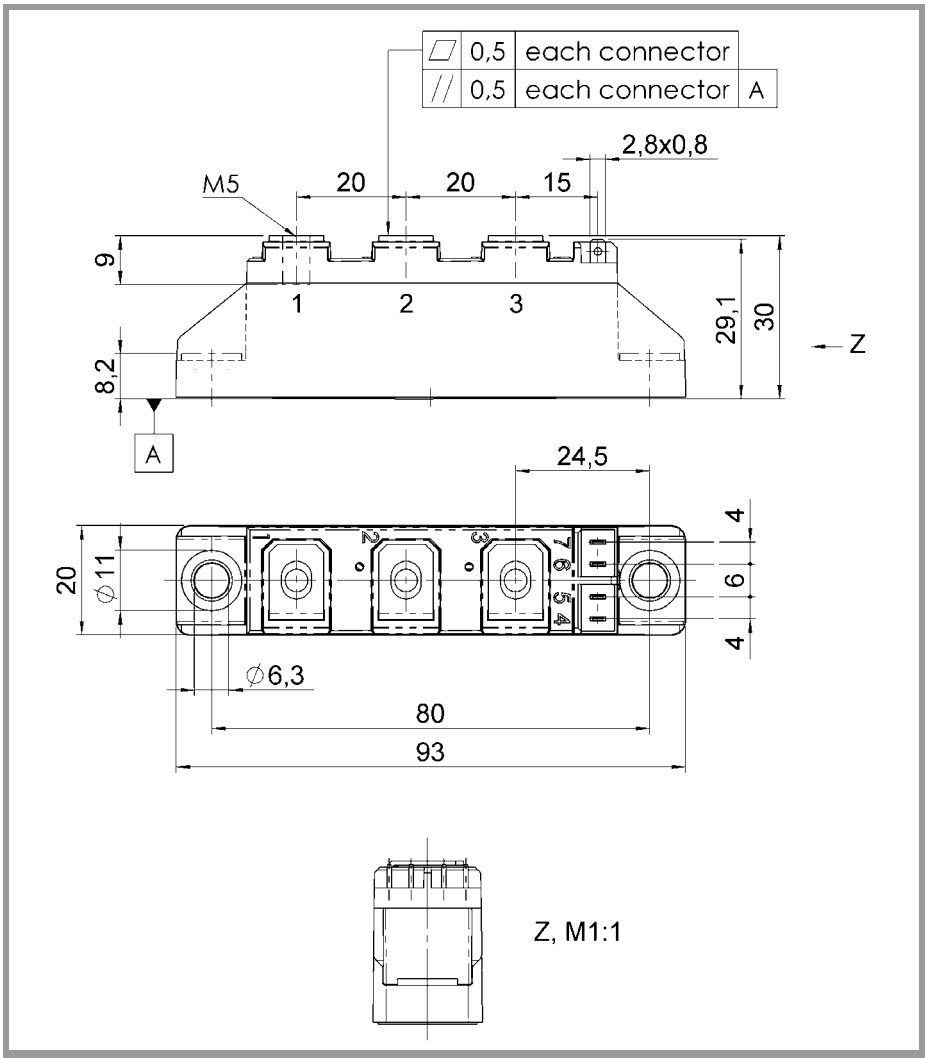


Fig. 9: Gate trigger characteristics



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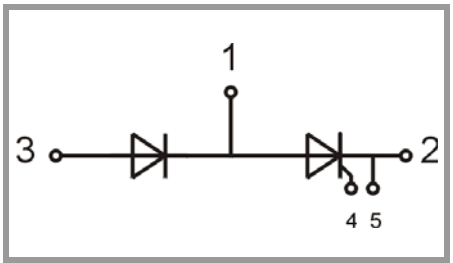

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